Product data sheet

1. General description

Dual ultrafast power diode in a TO263 (D2PAK) plastic package.

2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- · Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- · High thermal cycling performance
- · Low thermal resistance

3. Applications

- Home appliance power supply
- · Secondary rectification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			300			V
I _{O(AV)}	average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 155 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		20			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 157 °C; square-wave pulse; per diode		20			А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	220		А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode				А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	-	1.25	V
		I _F = 10 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	-	1	V
Dynamic	characteristics					-	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$		-	-	25	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		A1
3	A2	anode		<u> </u>
mb	К	mounting base; connected to cathode		.`` sym125

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV32EB-300P	TO263	BYV32EB-300PJ	Reel	800	TO263E (E)	26-May-2017
					TO263P (P)	12-Jun-2023

7. Marking

Table 4. Marking codes

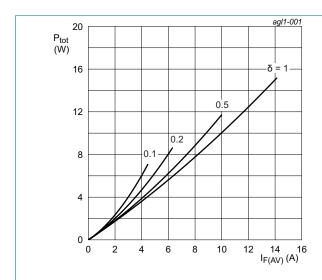
Type number	Marking codes			
	Assembly factory: E	Assembly factory: P		
BYV32EB-300P	BYV32EB 300P PJExxxx xx	BYV32EB 300P PJPxxxx xx		

8. Limiting values

Table 5. Limiting values

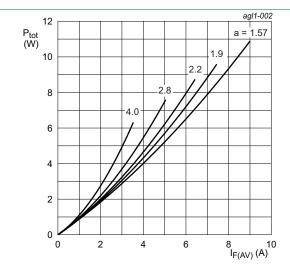
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak reverse voltage		300	V
crest working reverse voltage		300	V
reverse voltage	DC	300	V
average output current	$δ = 0.5$; $T_{mb} \le 155$ °C; square-wave pulse; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	20	Α
repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 157 °C; square-wave pulse; per diode	20	А
non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	220	А
	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	242	А
storage temperature		-65 to 175	°C
junction temperature		175	°C
	repetitive peak reverse voltage crest working reverse voltage reverse voltage average output current repetitive peak forward current non-repetitive peak forward current	repetitive peak reverse voltage crest working reverse voltage per voltage crest working reverse voltage per voltage per verse	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$



 $\begin{aligned} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.836 \text{ V; } R_s = 0.0168 \text{ } \Omega \end{aligned}$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.836 V; R_s = 0.0168 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

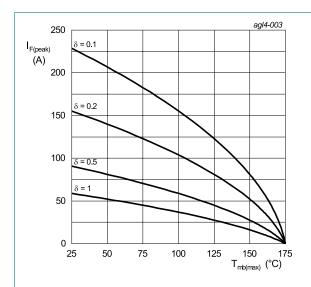


Fig. 3. Forward current as a function of mounting base temperature; maximum values; per diode

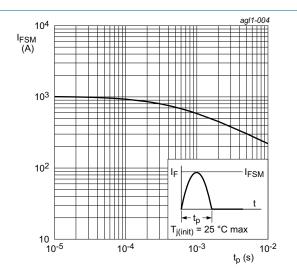
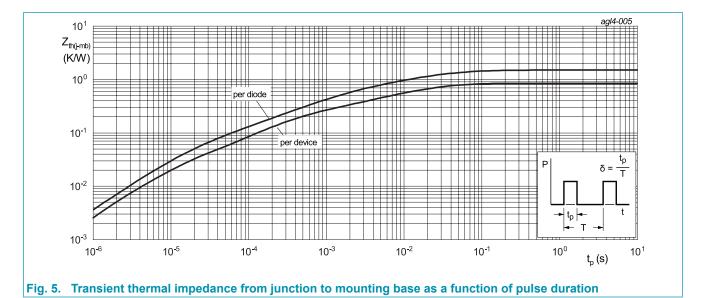


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

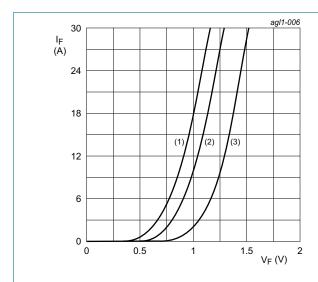
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	1.5	K/W
	mounting base	with heatsink compound; both diodes conducting; Fig. 5	-	-	0.85	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		·			
V_F	forward current	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	-	1.25	V
		I _F = 10 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	-	1	V
I _R	reverse current	$V_R = 300 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}$	-	-	20	μA
		V _R = 300 V; T _j = 125 °C; per diode	-	-	300	μA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	9	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	-	35	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	-	25	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	25	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; per diode; Fig. 7$	-	33	-	ns
I _{RM} peak reverse recovery current		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 7}}$	-	0.7	-	А
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 7}}$	-	1.1	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 25 °C; per diode; Fig. 7$	-	2.8	-	А
		$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 125 \text{ °C}$; per diode; Fig. 7	-	-	8	А



 V_o = 0.836 V; R_s = 0.0168 Ω (1) T_i = 125 °C; typical values

(2) $T_j = 125$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

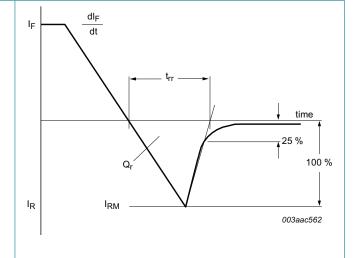
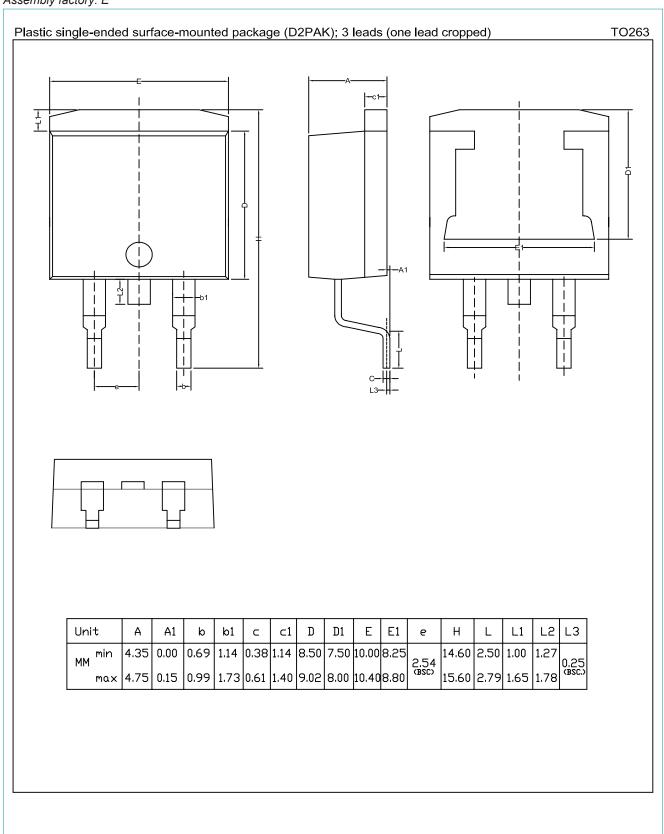


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

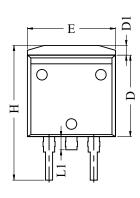
Assembly factory: E

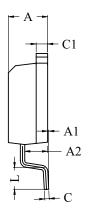


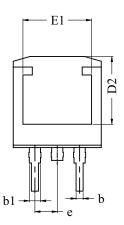
Assembly factory: P

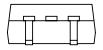


TO263









Dim	All Dimensions in Millimeters				
Dilli	Min	Тур	Max		
A	4.30	4.46	4.60		
A1	0	0.13	0.25		
A2	2.50	2.60	2.70		
b	0.70	0.80	0.90		
b1	1.10	1.27	1.45		
C	0.40	0.52	0.60		
C1	1.17	1.30	1.40		
D	9.10	9.25	9.40		
D1	1.00	1.10	1.30		
D2	7.40	7.70	8.00		
Е	9.80	10.00	10.20		
E1	7.60	7.80	8.00		
e		2.54 BSC			
Н	14.80	15.30	15.80		
L	2.10	2.47	2.80		
L1	1.30	1.50	1.70		

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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